

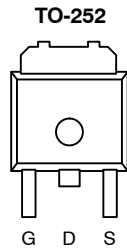


N-Channel 60-V (D-S), 175°C MOSFET, Logic Level

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a
60	0.022 @ $V_{GS} = 10$ V	30
	0.025 @ $V_{GS} = 4.5$ V	30

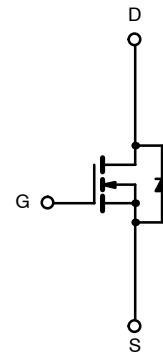
FEATURES

- TrenchFET® Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R_g Tested



Order Number:
SUD40N06-25L

Drain Connected to Tab



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175^\circ\text{C}$) ^b	$T_C = 25^\circ\text{C}$	I_D	30	A
	$T_C = 100^\circ\text{C}$		30	
Pulsed Drain Current		I_{DM}	100	
Continuous Source Current (Diode Conduction)		I_S	34	
Avalanche Current		I_{AR}	34	
Repetitive Avalanche Energy (Duty Cycle $\leq 1\%$)		E_{AR}	58	mJ
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	75	W
	$T_A = 25^\circ\text{C}$		1.4 ^b , 2.5 ^c	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Maximum Junction-to-Ambient	Free Air, FR4 Board Mount	R_{thJA}	60	$^\circ\text{C}/\text{W}$
	Free Air, Vertical Mount		110	
Maximum Junction-to-Case		R_{thJC}	2.0	

Notes:

- Package limited.
- Free air, vertical mount.
- Surface mounted on 1" x 1" FR4 Board, $t \leq 10$ sec.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

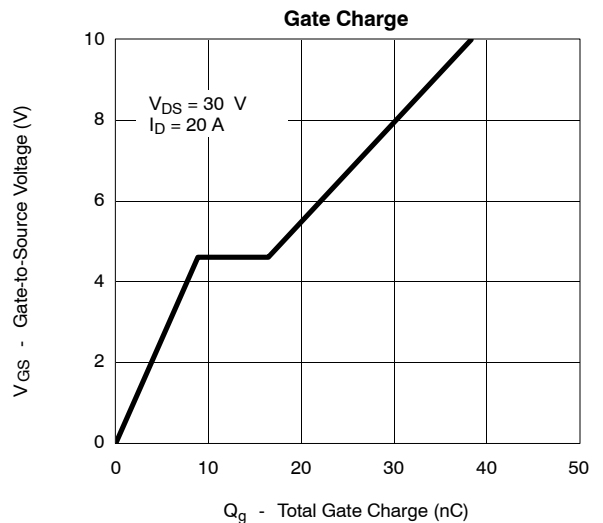
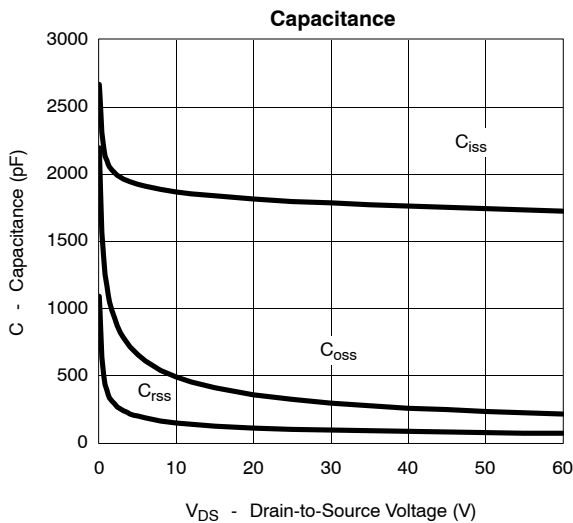
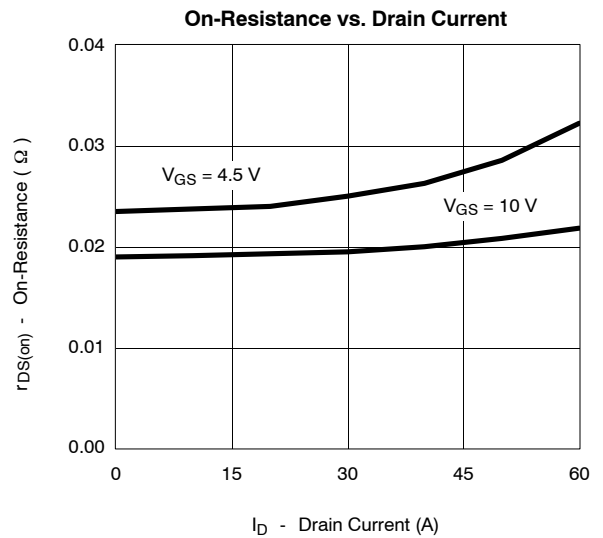
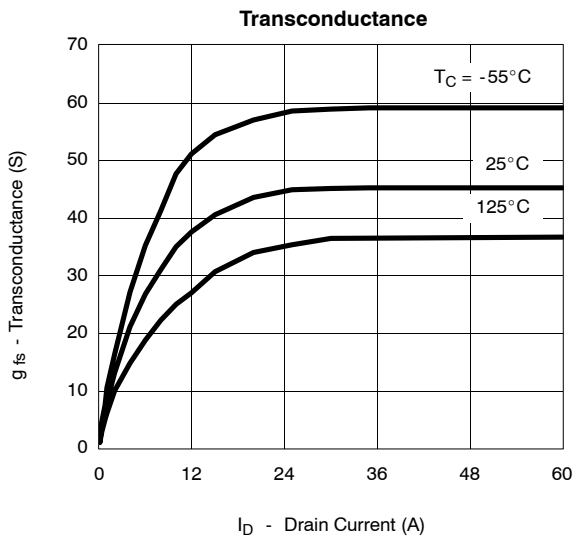
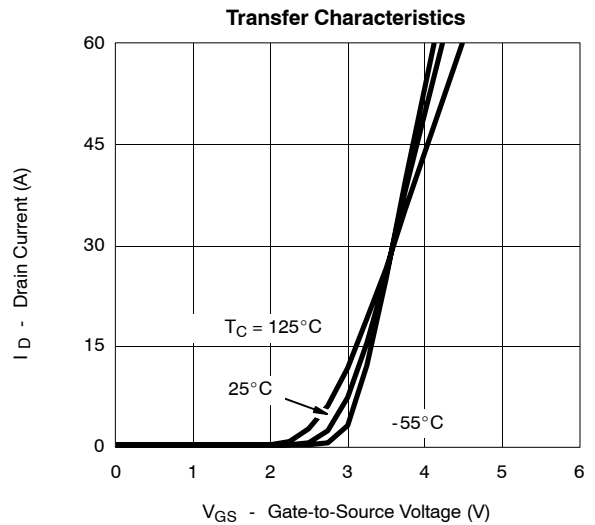
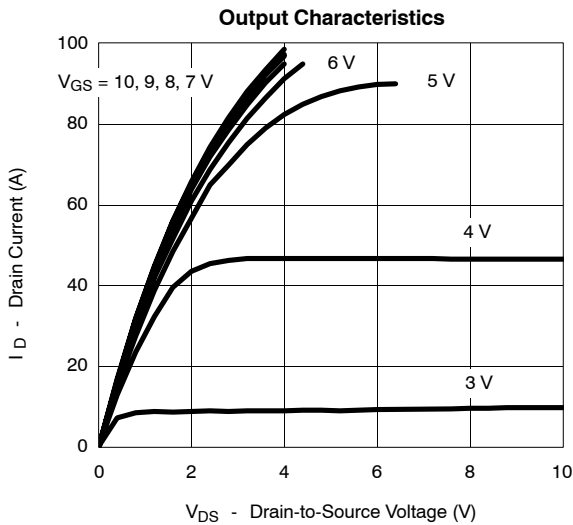
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0	2.0	3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			150	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	20			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A			0.022	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.043	
		V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.053	
		V _{GS} = 4.5 V, I _D = 20 A			0.025	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A				S
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		1800		pF
Output Capacitance	C _{oss}			350		
Reverse Transfer Capacitance	C _{rss}			100		
Total Gate Charge ^c	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 40 A		40	60	nC
Gate-Source Charge ^c	Q _{gs}			9		
Gate-Drain Charge ^c	Q _{gd}			10		
Gate Resistance	R _g		1		3.5	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.9 Ω I _D = 20 A, V _{GEN} = 10 V, R _G = 2.5 Ω		10	20	ns
Rise Time ^c	t _r			9	20	
Turn-Off Delay Time ^c	t _{d(off)}			28	50	
Fall Time ^c	t _f			7	15	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)						
Pulsed Current	I _{SM}				20	A
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		48	100	ns

Notes:

- For design aid only; not subject to production testing.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Independent of operating temperature.

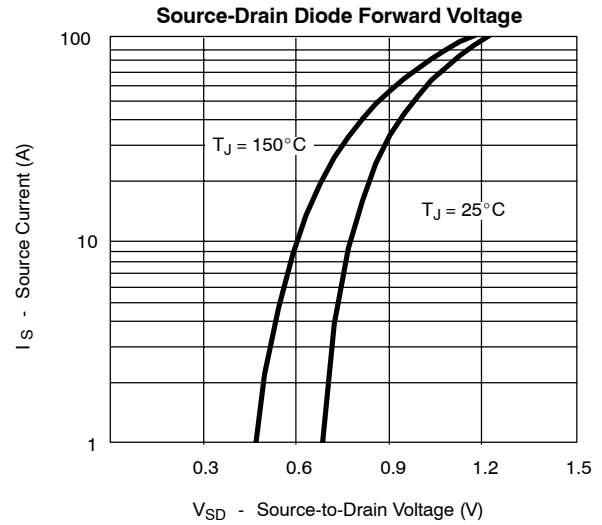
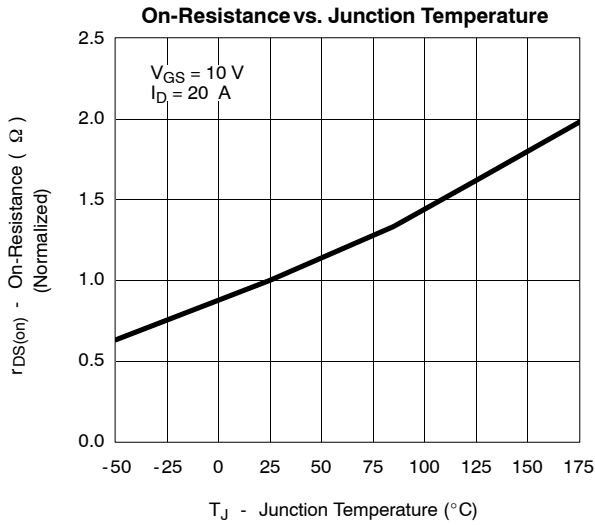


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





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THERMAL RATINGS

